

UT54ACS86/UT54ACTS86

Radiation-Hardened

Quadruple 2-Input Exclusive OR Gates

FEATURES

- 1.2μ radiation-hardened CMOS
 - Latchup immune
- High speed
- Low power consumption
- Single 5 volt supply
- Available QML Q or V processes
- Flexible package
 - 14-pin DIP
 - 14-lead flatpack

DESCRIPTION

The UT54ACS86 and the UT54ACTS86 are quadruple 2-input exclusive OR gates. The devices perform the Boolean function $Y = A \oplus B = \overline{A}B + A\overline{B}$ in positive logic.

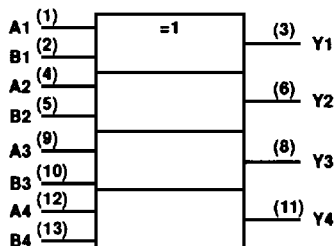
An application is as a true/complement element. If one of the inputs is low, the other input will be reproduced in true form at the output. If one of the inputs is high, the signal on the other input will be reproduced inverted at the output.

The devices are characterized over full military temperature range of -55°C to +125°C.

FUNCTION TABLE

INPUTS		OUTPUT
A	B	Y
L	L	L
L	H	H
H	L	H
H	H	L

LOGIC SYMBOL

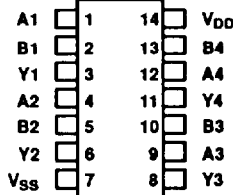


Note:

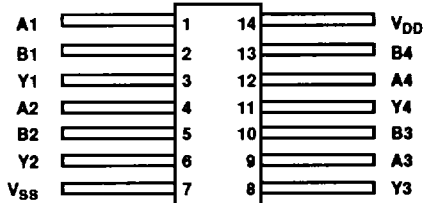
1. Logic symbol in accordance with ANSI/IEEE standard 91-1984 and IEC Publication 617-12.

PINOUTS

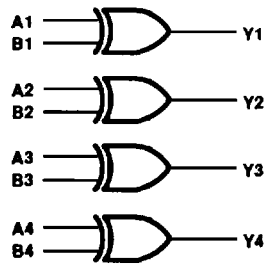
14-Pin DIP Top View



14-Lead Flatpack Top View



LOGIC DIAGRAM



RADIATION HARDNESS SPECIFICATIONS ¹

PARAMETER	LIMIT	UNITS
Total Dose	1.0E6	rads(Si)
SEU & SEL Threshold ²	80	MeV-cm ² /mg
Neutron Fluence	1.0E14	n/cm ²

Notes:

1. Logic will not latchup during radiation exposure within the limits defined in the table.
2. Device storage elements are immune to SEU affects.

ABSOLUTE MAXIMUM RATINGS

SYMBOL	PARAMETER	LIMIT	UNITS
V _{DD}	Supply voltage	-0.3 to 7.0	V
V _{I/O}	Voltage any pin	-.3 to V _{DD} +.3	V
T _{STG}	Storage Temperature range	-65 to +150	°C
T _J	Maximum junction temperature	+175	°C
T _{LS}	Lead temperature (soldering 5 seconds)	+300	°C
Θ _{JC}	Thermal resistance junction to case	20	°C/W
I _I	DC input current	± 10	mA
P _D	Maximum power dissipation	1	W

Note:

1. Stresses outside the listed absolute maximum ratings may cause permanent damage to the device. This is a stress rating only, functional operation of the device at these or any other conditions beyond limits indicated in the operational sections is not recommended. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

RECOMMENDED OPERATING CONDITIONS

SYMBOL	PARAMETER	LIMIT	UNITS
V _{DD}	Supply voltage	4.5 to 5.5	V
V _{IN}	Input voltage any pin	0 to V _{DD}	V
T _C	Temperature range	-55 to +125	°C

DC ELECTRICAL CHARACTERISTICS ⁷

($V_{DD} = 5.0V \pm 10\%$; $V_{SS} = 0V$ ⁶, $-55^{\circ}C < T_C < +125^{\circ}C$)

SYMBOL	PARAMETER	CONDITION	MIN	MAX	UNIT
V_{IL}	Low-level input voltage ¹ ACTS ACS			0.8 .3 V_{DD}	V
V_{IH}	High-level input voltage ¹ ACTS ACS		.5 V_{DD} .7 V_{DD}		V
I_{IN}	Input leakage current ACTS/ACT	$V_{IN} = V_{DD}$ or V_{SS}	-1	1	μA
V_{OL}	Low-level output voltage ³ ACTS ACS	$I_{OL} = 8.0mA$ $I_{OL} = 100\mu A$		0.40 0.25	V
V_{OH}	High-level output voltage ³ ACTS ACS	$I_{OH} = -8.0mA$ $I_{OH} = -100\mu A$.7 V_{DD} $V_{DD} - 0.25$		V
I_{OS}	Short-circuit output current ^{2,4} ACTS/ACS	$V_O = V_{DD}$ and V_{SS}	-200	200	mA
P_{total}	Power dissipation ^{8,9}	$C_L = 50pF$		1.8	mW/ MHz
I_{DDQ}	Quiescent Supply Current	$V_{DD} = 5.5V$		100	μA
C_{IN}	Input capacitance ⁵	$f = 1MHz @ 0V$		15	pF
C_{OUT}	Output capacitance ⁵	$f = 1MHz @ 0V$		15	pF

Notes:

- Functional tests are conducted in accordance with MIL-STD-883 with the following input test conditions: $V_{IH} = V_{IH}(min) + 20\%$, -0% ; $V_{IL} = V_{IL}(max) + 0\%$, -50% , as specified herein, for TTL, CMOS, or Schmitt compatible inputs. Devices may be tested using any input voltage within the above specified range, but are guaranteed to $V_{IH}(min)$ and $V_{IL}(max)$.
- Supplied as a design limit but not guaranteed or tested.
- Per MIL-M-38510, for current density $\leq 5.0E5$ amps/cm², the maximum product of load capacitance (per output buffer) times frequency should not exceed 3,765 pF MHz.
- Not more than one output may be shorted at a time for maximum duration of one second.
- Capacitance measured for initial qualification and when design changes may affect the value. Capacitance is measured between the designated terminal and V_{SS} at frequency of 1MHz and a signal amplitude of 50mV rms maximum.
- Maximum allowable relative shift equals 50mV.
- All specifications valid for radiation dose $\leq 1E6$ rads(Si).
- Power does not include power contribution of any TTL output sink current.
- Power dissipation specified per switching output

AC ELECTRICAL CHARACTERISTICS ²

($V_{DD} = 5.0V \pm 10\%$; $V_{SS} = 0V$ ¹, $-55^{\circ}C < T_C < +125^{\circ}C$)

SYMBOL	PARAMETER	MINIMUM	MAXIMUM	UNIT
t _{pHL}	Data to input	1	14	ns
t _{pLH}	Data to input	1	13	ns

Notes:

1. Maximum allowable relative shift equals 50mV.
2. All specifications valid for radiation dose $\leq 1E6$ rads(Si).